

Title (en)
TRANSISTOR WITH INTERDIGITAL ELECTRODES, COMPRISING A GATE TERMINAL CONNECTED BY A PLURALITY OF VERTICAL VIAS TO THE GATE ELECTRODES

Title (de)
TRANSISTOR MIT INTERDIGITALELEKTRODEN MIT EINEM GATE-ANSCHLUSS, DER ÜBER MEHRERE VERTIKALE DURCHKONTAKTIERUNGEN MIT DEN GATE-ELEKTRODEN VERBUNDEN IST

Title (fr)
TRANSISTOR A ELECTRODES INTERDIGITEES, COMPRENANT UN TERMINAL DE GRILLE CONNECTE PAR UNE PLURALITE DE VIAS VERTICAUX AUX ELECTRODES DE GRILLE

Publication
EP 4173033 A1 20230503 (FR)

Application
EP 21737725 A 20210615

Priority
• FR 2006863 A 20200630
• FR 2021051069 W 20210615

Abstract (en)
[origin: WO2022003265A1] The invention relates to a field-effect transistor (100) having an interdigital structure and comprising: several elementary transistor cells (50) arranged in parallel, each elementary cell comprising a source electrode (1), a drain electrode (3) and a gate electrode (2) interposed between the source and drain electrodes, a source terminal (10) and a drain terminal (30) respectively connected to the source electrodes (1) and to the drain electrodes (3) of the elementary cells (50), a gate terminal (20) connected to the gate electrodes (2) of the elementary cells. The field-effect transistor (100) comprises only vertical conductive vias for connecting the gate electrodes to the gate terminal, and the gate terminal (20) is arranged vertically in line with all or part of the elementary cells (50).

IPC 8 full level
H01L 23/48 (2006.01); **H01L 23/482** (2006.01); **H01L 23/522** (2006.01); **H01L 29/423** (2006.01)

CPC (source: EP US)
H01L 23/481 (2013.01 - EP US); **H01L 23/482** (2013.01 - US); **H01L 23/4824** (2013.01 - EP); **H01L 23/498** (2013.01 - US); **H01L 23/5226** (2013.01 - EP US); **H01L 24/29** (2013.01 - US); **H01L 24/32** (2013.01 - US); **H01L 27/088** (2013.01 - US); **H01L 29/402** (2013.01 - EP); **H01L 29/7786** (2013.01 - EP); **H01L 29/2003** (2013.01 - EP); **H01L 29/41766** (2013.01 - EP); **H01L 2224/29139** (2013.01 - US); **H01L 2224/32227** (2013.01 - US)

Citation (search report)
See references of WO 2022003265A1

Designated contracting state (EPC)
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)
BA ME

Designated validation state (EPC)
KH MA MD TN

DOCDB simple family (publication)
FR 3112025 A1 20211231; FR 3112025 B1 20230421; EP 4173033 A1 20230503; US 2023253401 A1 20230810; WO 2022003265 A1 20220106

DOCDB simple family (application)
FR 2006863 A 20200630; EP 21737725 A 20210615; FR 2021051069 W 20210615; US 202118003486 A 20210615